

NTTFS4800N

Power MOSFET

30 V, 32 A, Single N-Channel, μ 8FL

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- DC-DC Converters
- Point of Load
- Power Load Switch
- Notebook Battery Management
- Motor Control

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	30	V	
Gate-to-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JA}$ (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	8.3	A
		$T_A = 85^{\circ}\text{C}$		6.0	
$T_A = 25^{\circ}\text{C}$		P_D	2.2	W	
$T_A = 25^{\circ}\text{C}$		I_D	11.8	A	
$T_A = 85^{\circ}\text{C}$			8.5		
$T_A = 25^{\circ}\text{C}$		P_D	4.5	W	
Continuous Drain Current $R_{\theta JA}$ (Note 2)		$T_A = 25^{\circ}\text{C}$	I_D	5.0	A
		$T_A = 85^{\circ}\text{C}$		3.6	
Power Dissipation $R_{\theta JA}$ (Note 2)		$T_A = 25^{\circ}\text{C}$	P_D	0.86	W
Continuous Drain Current $R_{\theta JC}$ (Note 1)		$T_C = 25^{\circ}\text{C}$	I_D	32	A
	$T_C = 85^{\circ}\text{C}$	23			
Power Dissipation $R_{\theta JC}$ (Note 1)	$T_C = 25^{\circ}\text{C}$	P_D	33.8	W	
Pulsed Drain Current	$T_A = 25^{\circ}\text{C}, t_p = 10\text{ }\mu\text{s}$	I_{DM}	57	A	
Current Limited by Pkg.	$T_A = 25^{\circ}\text{C}$	$I_{DmaxPkg}$	20	A	
Operating Junction and Storage Temperature		T_J, T_{stg}	-55 to +150	$^{\circ}\text{C}$	
Source Current (Body Diode)		I_S	28	A	
Drain to Source DV/DT		dV/dt	6.0	V/ns	
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^{\circ}\text{C}, V_{DD} = 50\text{ V}, V_{GS} = 10\text{ V}, I_L = 27\text{ A}_{pk}, L = 0.1\text{ mH}, R_G = 25\text{ }\Omega$)		E_{AS}	36.6	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^{\circ}\text{C}$	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.

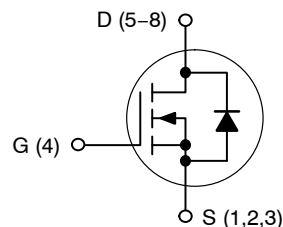


ON Semiconductor®

<http://onsemi.com>

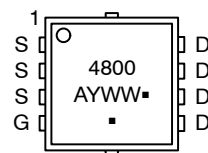
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	20 m Ω @ 10 V	32 A
	27 m Ω @ 4.5 V	

N-Channel MOSFET



WDFN8
(μ 8FL)
CASE 511AB

MARKING DIAGRAM



4800 = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NTTFS4800NTAG	WDFN8 (Pb-Free)	1500/Tape & Reel
NTTFS4800NTWG	WDFN8 (Pb-Free)	5000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTTFS4800N

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	3.7	°C/W
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	56.7	
Junction-to-Ambient – Steady State (Note 4)	$R_{\theta JA}$	146	
Junction-to-Ambient – ($t \leq 10$ s) (Note 3)	$R_{\theta JA}$	27.8	

3. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.

4. Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
-----------	--------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			16.2		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	1.5		3.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			5.7		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V to }11.5\text{ V}$	$I_D = 20\text{ A}$		11.1	m Ω
			$I_D = 10\text{ A}$		11	
		$V_{GS} = 4.5\text{ V}$	$I_D = 20\text{ A}$		18	
			$I_D = 10\text{ A}$		17	
Forward Transconductance	g_{FS}	$V_{DS} = 1.5\text{ V}, I_D = 20\text{ A}$		28		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 15\text{ V}$		964		pF
Output Capacitance	C_{oss}			225		
Reverse Transfer Capacitance	C_{rss}			125		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		8.4		nC
Threshold Gate Charge	$Q_{G(TH)}$			1.2		
Gate-to-Source Charge	Q_{GS}			3.4		
Gate-to-Drain Charge	Q_{GD}			3.8		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		16.6		nC

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\text{ }\Omega$		11.1		ns
Rise Time	t_r			21.8		
Turn-Off Delay Time	$t_{d(off)}$			14		
Fall Time	t_f			3.4		

5. Pulse Test: pulse width = 300 μs , duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

NTTFS4800N

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
-----------	--------	----------------	-----	-----	-----	------

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 15\text{ A}, R_G = 3.0\ \Omega$		7.6		ns
Rise Time	t_r			19.5		
Turn-Off Delay Time	$t_{d(off)}$			19		
Fall Time	t_f			2.1		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 20\text{ A}$	$T_J = 25^\circ\text{C}$		0.93	1.2	V
			$T_J = 125^\circ\text{C}$		0.83		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 20\text{ A}$			16.8		ns
Charge Time	t_a				8.7		
Discharge Time	t_b				8.1		
Reverse Recovery Charge	Q_{RR}				6.8		nC

PACKAGE PARASITIC VALUES

Source Inductance	L_S	$T_A = 25^\circ\text{C}$		0.66		nH
Drain Inductance	L_D			0.20		
Gate Inductance	L_G			1.5		
Gate Resistance	R_G			1.5	3.0	Ω

5. Pulse Test: pulse width = 300 μs , duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

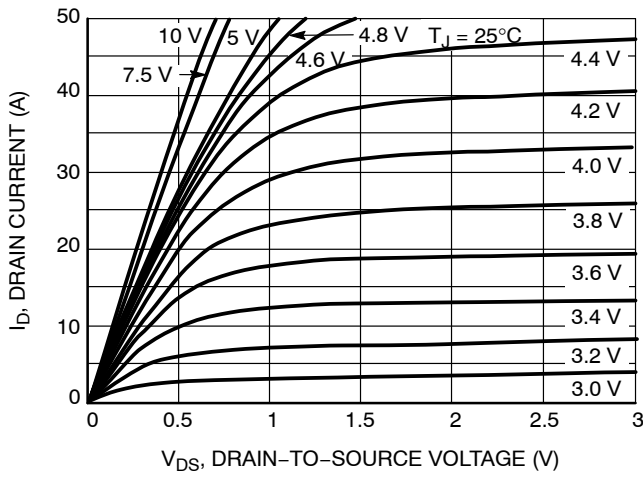


Figure 1. On-Region Characteristics

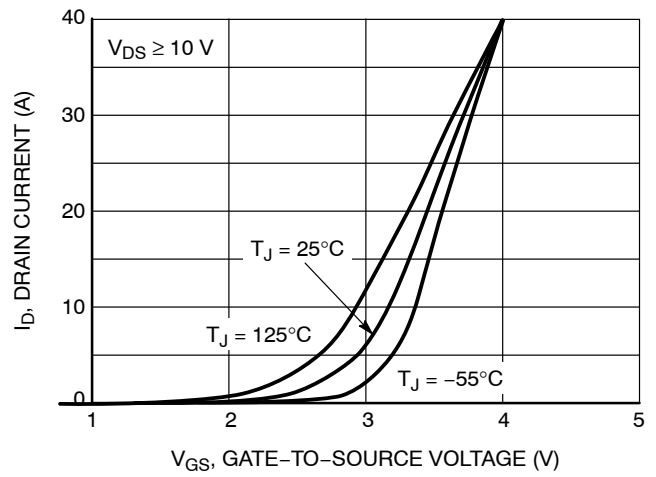


Figure 2. Transfer Characteristics

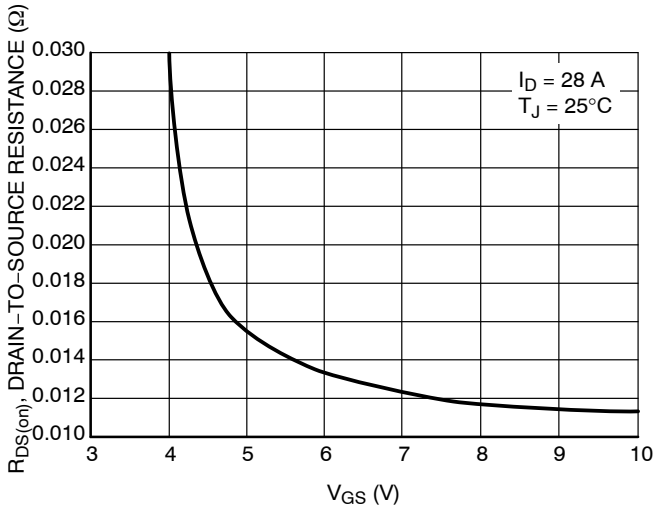


Figure 3. On-Resistance vs. V_{GS}

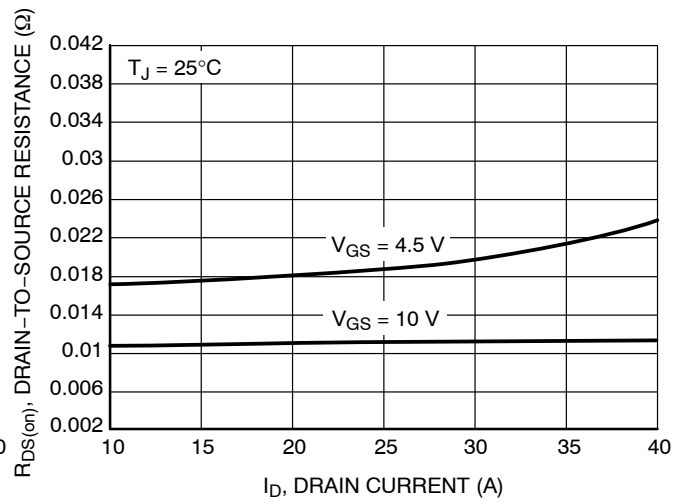


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

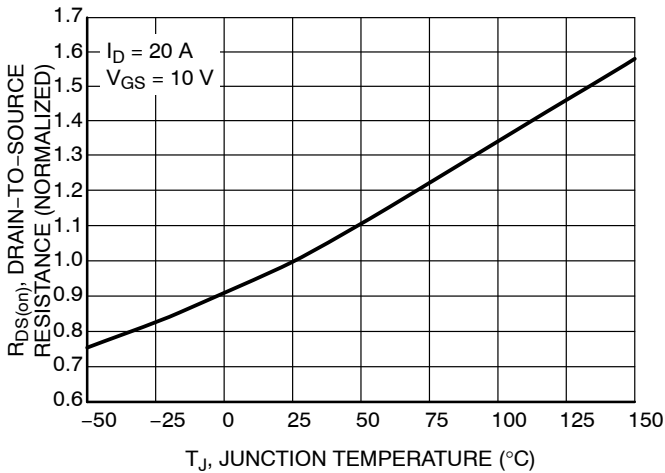


Figure 5. On-Resistance Variation with Temperature

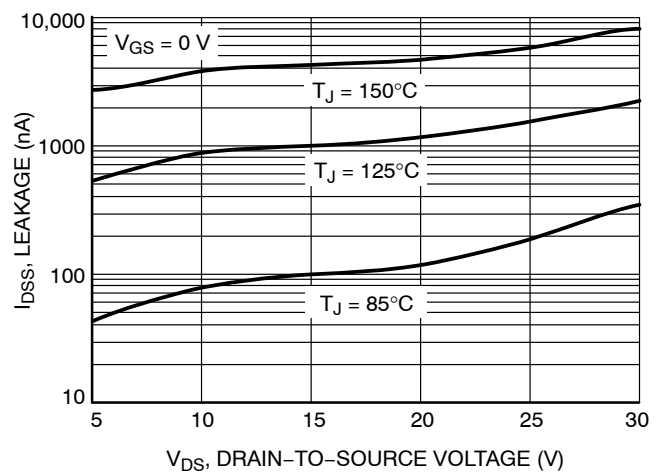


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

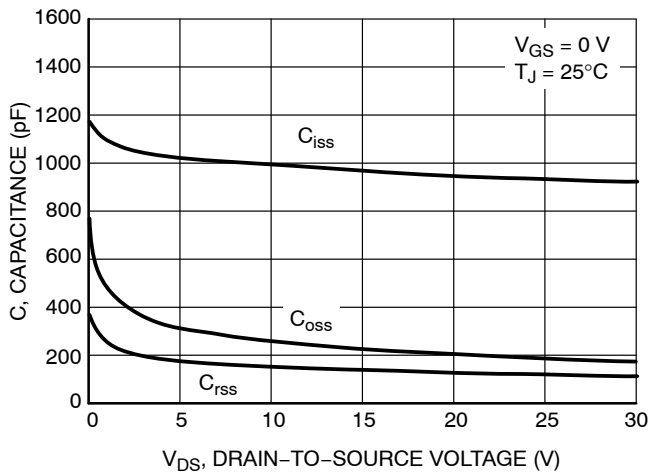


Figure 7. Capacitance Variation

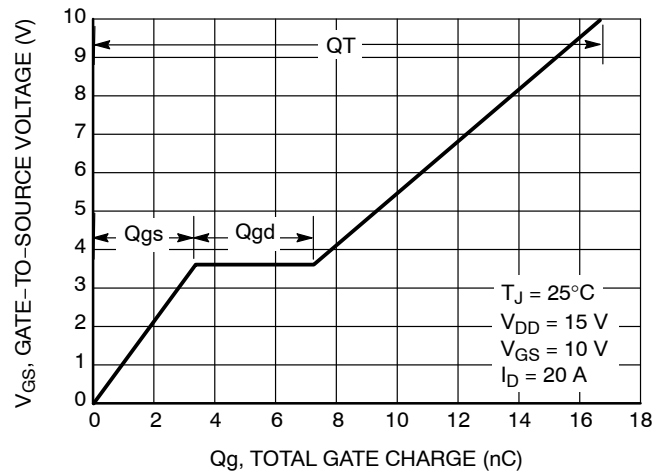


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

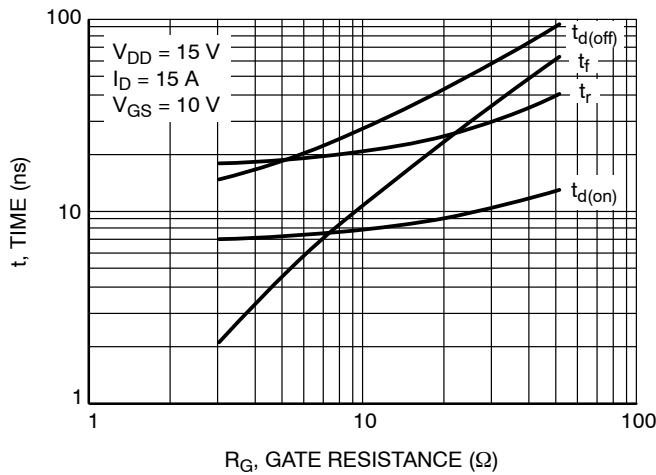


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

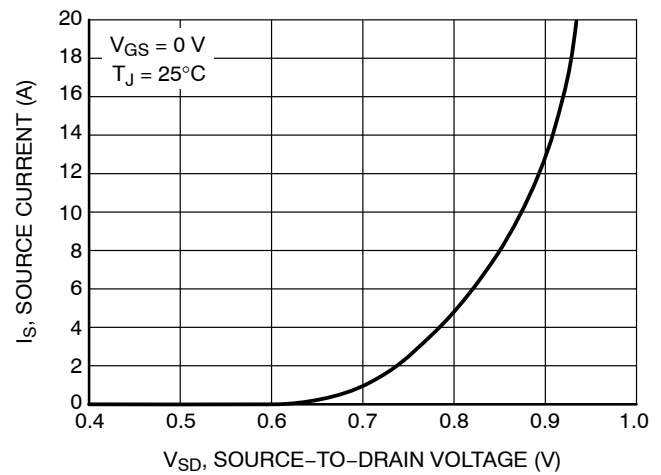


Figure 10. Diode Forward Voltage vs. Current

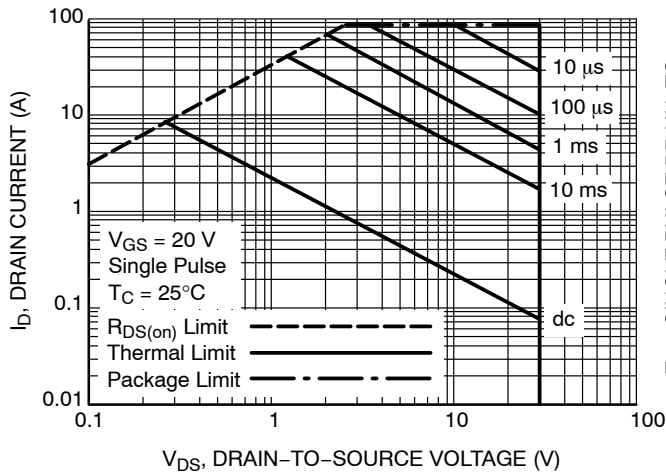


Figure 11. Maximum Rated Forward Biased Safe Operating Area

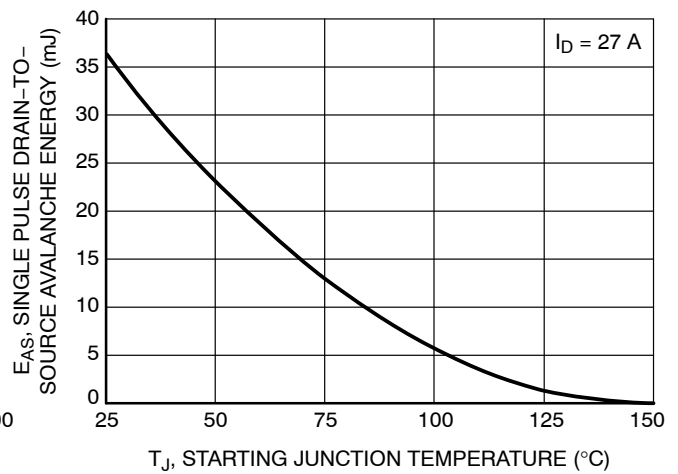


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

NTTFS4800N

TYPICAL CHARACTERISTICS

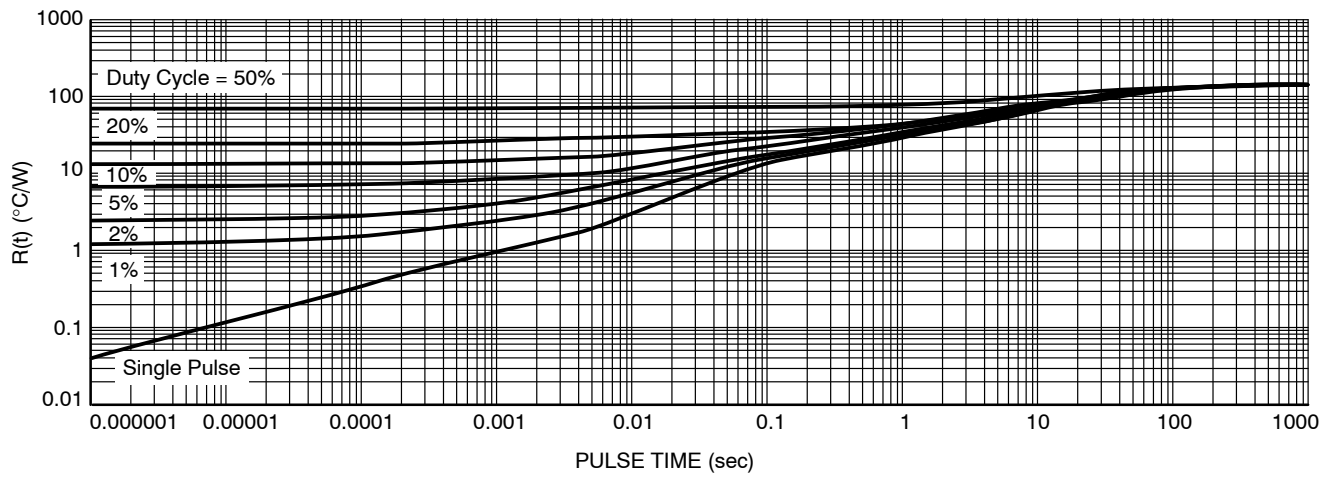
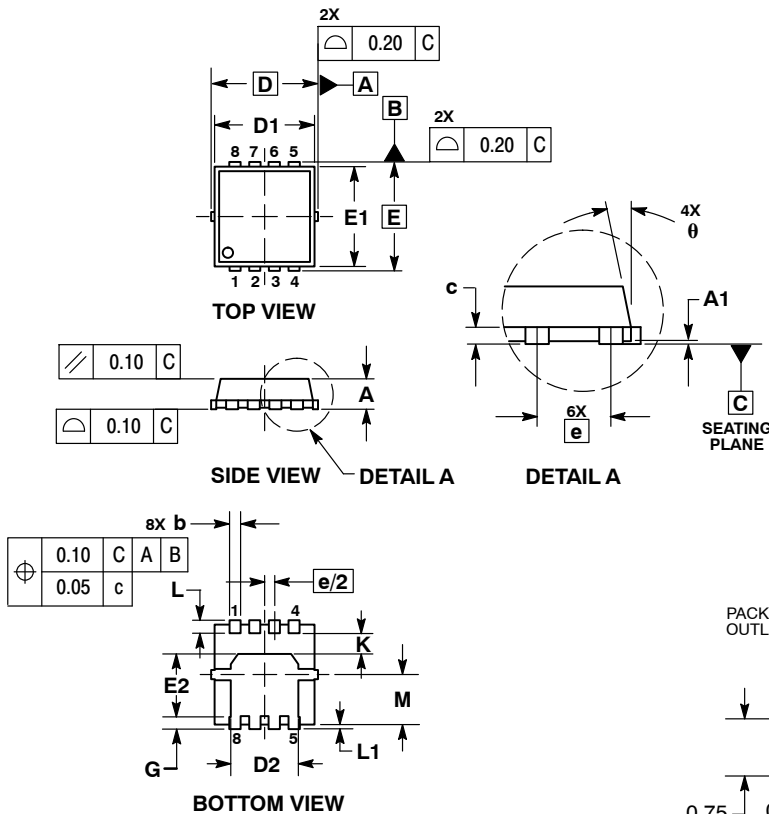


Figure 13. Thermal Response

NTTFS4800N

PACKAGE DIMENSIONS

WDFN8 3.3x3.3, 0.65P
CASE 511AB-01
ISSUE B

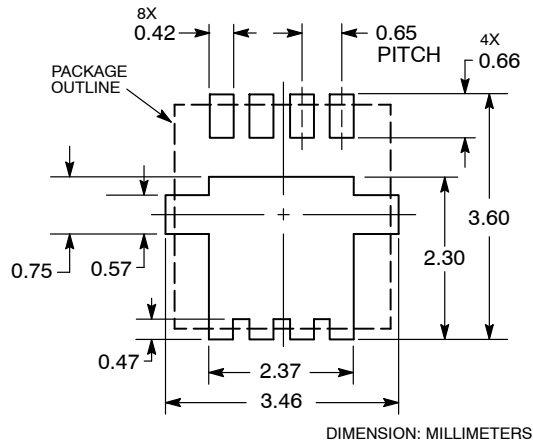


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031
A1	0.00	---	0.05	0.000	---	0.002
b	0.23	0.30	0.40	0.009	0.012	0.016
c	0.15	0.20	0.25	0.006	0.008	0.010
D	3.30 BSC			0.130 BSC		
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
E	3.30 BSC			0.130 BSC		
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
e	0.65 BSC			0.026 BSC		
G	0.30	0.41	0.51	0.012	0.016	0.020
K	0.64	---	---	0.025	---	---
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
M	1.40	1.50	1.60	0.055	0.059	0.063
θ	0 °	---	12 °	0 °	---	12 °

SOLDERING FOOTPRINT*



DIMENSION: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative